



Effect of aluminum addition on the densification behavior and mechanical properties of synthesized high-purity nano-laminated Ti_3SiC_2 through spark plasma sintering



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ABSTRACT

To reveal the effect of Al content on the purity and mechanical properties of Ti_3SiC_2 , the powder mixture of $1\text{Ti}/1.2\text{Si}/2\text{TiC}/x\text{Al}$ ($x = 0-0.4$) were sintered to synthesize Ti_3SiC_2 through spark plasma sintering (SPS). The sintering process was conducted at $1150\text{ }^\circ\text{C}$ for 8 min under a pressure of 40 MPa. To evaluate the phase constituents and morphology of the sintered samples, X-ray diffraction and field emission scanning electron microscopy were used. It was found that addition of Al from 0.2 to 0.4 mol in the starting powder mixture led to synthesis of high-purity Ti_3SiC_2 . Besides, with increasing the Al content in the starting powder mixture, the densification behavior of sintered samples was promoted. The results showed that the Vickers microhardness of high-purity samples became almost same at higher loads and moreover the measured Young's modulus (E) of the high-purity Ti_3SiC_2 samples were near to each other and increased with promoting the densification.

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1. Introduction

Because of unusual combination properties of both metals and ceramics, Ti_3SiC_2 have been attracted a lot of attentions for recent years. Ti_3SiC_2 has better electrical and thermal conductivity than Ti and TiC and this ternary compound is elastically quite stiff with low density (4.52 g cm^{-3}). Its specific stiffness is comparable to that of Si_3N_4 and three times that of Ti. Ti_3SiC_2 is readily machinable, resistant to thermal shock and refractory. Also it is unusually damage tolerant which is caused by kink bands and different multiple energy-absorbing mechanisms such as diffuse micro-cracking, delamination, crack deflection, grain buckling, micro-cracking, delamination, crack deflection, grain buckling, grain pull-out, and grain push-out [1–5]. The amounts of hardness, Young's modulus and fracture toughness of Ti_3SiC_2 , reported in the literatures are 4 GPa [1,3,6], 320–334 GPa [1,7,8] and $6\text{ MPa m}^{1/2}$ [3], respectively. Ti_3SiC_2 is a likely candidate for structural applications at elevated temperatures, such as heating elements, turbine blades, stators and rotating electrical contacts like commutating brushes for AC motors [2].

Attempts to synthesize high-purity Ti_3SiC_2 bulk samples had been accompanied with the auxiliary phases such as TiC and SiC in the final samples, therefore synthesis of high-purity Ti_3SiC_2 used to be a great challenge [9]. Thence many researchers have been employed various methods to synthesize high-purity Ti_3SiC_2 in the form of bulk material such as HIP [10,11], hot pressing (HP) [12,13], infiltration [14–17], vacuum sintering [18] and spark plasma sintering (SPS) [19,20]. Among these techniques, the SPS method which is known as the pulse discharge sintering (PDS), is conducted at relatively low temperatures and short times with fine micro-structure relative to others conventional methods. Due to the presence of plasma, the localized temperature was reported up to $10000\text{ }^\circ\text{C}$ during spark plasma sintering process [21,22]. There are various starting powder mixtures in order to synthesize high-purity Ti_3SiC_2 , Ti/Si/C [23–25], Ti/Si/TiC [19,24,26,27], Ti/SiC/C [24,28], Ti/SiC/TiC [29], Ti/TiSi₂/TiC [30], TiH₂/Si/TiC [31] and furthermore Si/TiC [32], which in turn these compositions have great effects on the amounts of secondary phases in the sintered samples. Moreover, in order to improve the content of Ti_3SiC_2 in the final product and lowering the synthesis temperature, addition of Al (it has low-melting temperature relative to another starting powders) was accomplished. Small addition of Al into the starting powder mixtures can improve the synthesis of Ti_3SiC_2 via forming an Al–Si alloy containing 0–44% Si at $1000\text{ }^\circ\text{C}$ in the Al–C–Si–Ti

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quaternary system [20,26]. Zhou et al. [26] synthesized single-phase Ti_3SiC_2 by sintering starting powder mixture of 1Ti/1Si/2TiC/0.2Al at 1250–1300 °C. They reported that small variation of additional Al enabled TiC auxiliary phase formation. Ghosh et al. [33] fabricated nearly single-phase Ti_3SiC_2 and Ti_3SiC_2 -TiC composites with the starting powder mixture of Ti/Si/TiC along with 0.2 mol Al at 1250 °C. They observed some bright agglomerates which were rich in Al. Zhang et al. [34] reported that optimum molar content of Al was in the range of 0.1–0.3 with starting powder mixture of Ti/Si/C and with increasing the Al content to 0.4, the TiC phase was formed again. As discussed above, in order to synthesize high-purity Ti_3SiC_2 ternary compound with the starting powder mixture of Ti/Si/TiC/Al, the optimum amount of Al was reported to be 0.2 mol. But recently, Gao et al. [35] synthesized $\text{Ti}_3(\text{Al}_{1-x}\text{Si}_x)\text{C}_2$ ($x = 0-1$) solid solution from starting powder mixture of Ti/Si/TiC/Al in the temperature range of 1500–1600 °C. The loss of density was reported with simultaneous increment of Al and reduction of Si contents in the starting powder mixtures. Besides, they reported uniform distribution of Ti, Si and Al elements in the microstructure. As seen, there are some different and complex results about the addition of Al contents.

In this study, to reveal the effect of Al content on the purity of Ti_3SiC_2 , microstructure, lattice parameter, density and mechanical properties of prepared samples through SPS, the starting powder mixtures of 1Ti/1.2Si/2TiC/xAl ($x = 0, 0.1, 0.2, 0.3$ and 0.4) were sintered at 1150 °C for 8 min. In addition, the effect of different Al contents on high-temperature behavior (initiation and completion of densification process) of samples was investigated.

2. Materials and methods

Commercial powders of Ti (<40 μm , >99%), Si (2–5 μm , >98%), TiC (3–5 μm) and Al (130 μm , 99%) were used as the starting powders. The molar ratios of starting powders were selected to 1Ti/1.2Si/2TiC/xAl with $x = 0, 0.1, 0.2, 0.3$ and 0.4 . In order to compensate the loss of Si at higher temperatures, off-stoichiometry molar content of Si were used. The powder mixtures were ball-milled at room temperature for 5 h using a planetary ball mill with WC jars and zirconia balls under argon protective atmosphere. The ball to powder ratio was set at 10:1 and the milling speed was 200 rpm. Then the ball-milled powders were filled in a cylindrical graphite mold (30 mm in diameter) and sintered in vacuum by using SPS apparatus. The starting applied pressure was set at 40 MPa and the heating rate is controlled about 20–25 °C.min⁻¹. The sintering temperature was maintained at 1150 °C for 8 min. The pyrometer used to measure the temperature in our study, was focused on the center of mold through a drilled hole on the upper graphite punch. The calibration method for measuring the temperature was drilling a hole on upper punch from the top surface to 5 mm at the end of punch. Two graphite layers (0.2 mm in thickness) were placed between the punches and samples. The samples labeled as A0, A0.1, A0.2, A0.3 and A0.4 for SPS sintered powder mixtures with Al contents of 0, 0.1, 0.2, 0.3 and 0.4, respectively. To study the sintering behavior of bulk samples, the displacement of the shifting upper ram of the SPS apparatus was recorded while the lower ram was fixed.

After sintering, the samples were ground to remove the graphite layer. Then the phase constitution identification were performed using X-ray diffraction (XRD) experiments by PHILIPS PW1730 using Cu-K α radiation at 30 kV and 40 mA and step size of 0.05° s⁻¹. The quantification amounts of the formed phases along with the related lattice parameters were determined with the Rietveld refinement [36]. In addition to the Rietveld refinement, the quantification amounts of phases were calculated by the standard additive methods [27] as well to validate the results. The relative

densities of samples were determined by Archimedes method according to ASTM B311-93 (2002) e1 standard. Subsequently, the samples were polished and etched by a solution of H₂O:HNO₃:HF (1:1:1) to expose the Ti_3SiC_2 grains. The morphology and microstructure of samples were observed and analyzed by using field emission scanning electron microscope (FE-SEM) equipped with energy dispersive spectroscopy (EDS). The Young's modulus of samples was measured by Pulse-Echo method, using ASTM E797-95. The Vickers hardness tests were performed at 0.5, 1, 3, 5 and 10 N loads with a dwelling time of 10 s and then in order to observe the damage zones and crack propagation from the corners of indentations, an optical microscope (OM) was employed. The values of Young's modulus and microhardness are the average of 5 measurements.

3. Result and discussion

3.1. X-ray diffraction patterns

Fig. 1 illustrates the XRD patterns of SPS sintered samples with different Al contents. It can be observed that with decreasing Al content lower than 0.2 mol (A0 and A0.1 samples), the synthesis of Ti_3SiC_2 has been found more difficult. When no Al content was used in the starting powder mixture, no Ti_3SiC_2 was formed in the SPS sintered sample (A0 sample). As seen in Fig. 1 (a), the main peaks of A0 sample were related to the Ti and SiC phases. The Si in the starting powder mixture was reacted to the graphite layer between powder and punch and therefore the SiC phase was formed. In addition to observed peaks, the TiC, Ti_5Si_3 and TiSi_2 peaks were identified. With the addition of Al content to 0.1 mol (A0.1 sample), the Ti, SiC and TiSi_2 peaks disappeared and the Ti_3SiC_2 peaks began to intensifying at $2\theta \approx 39.53^\circ$ (Fig. 1 (b)). It is clearly seen that with addition of Al, the formation of intermediate Ti_5Si_3 phase was promoted which improved the Ti_3SiC_2 content in the sintered samples. With increasing Al content to 0.2, 0.3 and 0.4 mol (A0.2, A0.3 and A0.4 samples), as shown in Fig. 1 (c)–(e), all peaks were related to Ti_3SiC_2 with the main peak at $2\theta \approx 39.5^\circ$ and no other secondary phases were identified. According to the XRD results, it is clearly seen that Al played a key role on the synthesis of Ti_3SiC_2 and decreasing the sintering temperature as well. As the Al content was decreased to zero or 0.1 mol, the sufficient sintering temperature for the synthesis of high-purity Ti_3SiC_2 was increased.

The weight percentage amounts of phases formed in the A0.1 sample, calculated by the Rietveld refinement and related profile agreement factor (χ^2 , goodness of fit) and standard additive method are presented in Table 1. As it can be seen, due to overlapping peaks in the diffraction patterns, the discrepancies of calculated weight percentage amounts were significantly high. In this situation, the Rietveld refinement is more acceptable, because of its capability to refine complicated and low symmetry structures with many overlapping peaks.

The lattice parameters and lattice volume of high-purity Ti_3SiC_2 samples, calculated with the Rietveld refinement, are presented in Table 2 along with profile agreement factor. As it can be observed, with decreasing Al content, the lattice volume of Ti_3SiC_2 slightly increased. The lattice parameters (a and c) were not changed significantly. These lattice parameters and lattice volumes are in good agreement with the ones reported by Gao et al. [35]. They expressed that with increasing the Si content in the starting powder mixture, the c-lattice parameters were decreased whereas no change was observed in the a-lattice parameters.

3.2. Microstructural analysis

To evaluate the effect of Al addition on the microstructure of

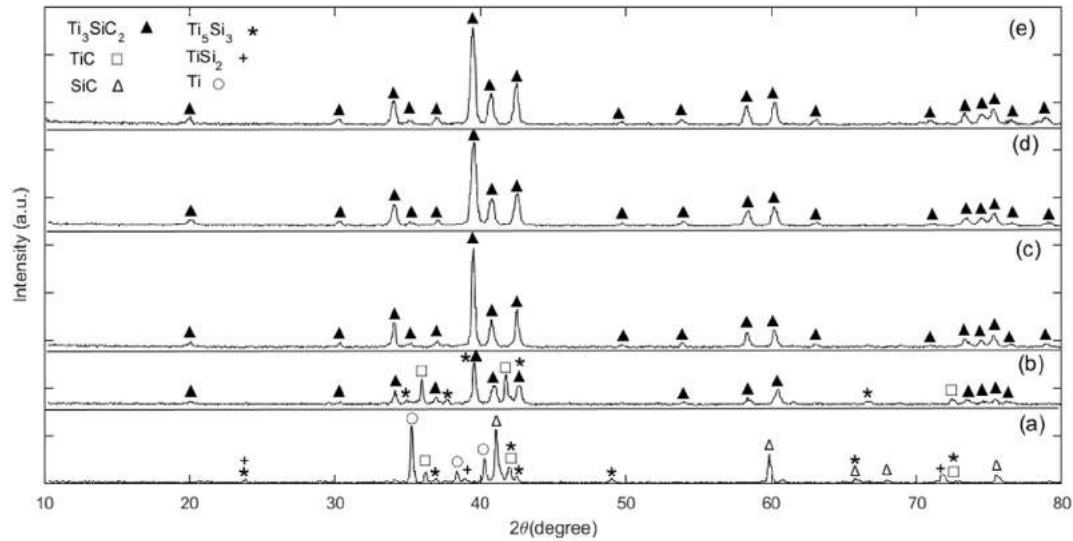


Fig. 1. XRD patterns of (a) A0, (b) A0.1, (c) A0.2, (d) A0.3 and (e) A0.4 samples.

Table 1

Weight percentage amounts of formed phases in the A0.1 samples with the Rietveld refinements and standard additive method.

Sample	Rietveld Refinement				Std. Add. Method		
	Ti ₃ SiC ₂ (%)	TiC(%)	Ti ₅ Si ₃ (%)	χ ²	Ti ₃ SiC ₂ (%)	TiC(%)	Ti ₅ Si ₃ (%)
A0.1	30	31	39	4.39	62.34	18.4	19.26

Table 2

Summary of lattice parameters and lattice volume obtained from Rietveld refinements.

Sample	Rietveld Refinement				
	a = b(Å)	c(Å)	Lattice volume(Å ³)	c/a	χ ²
A0.2	3.068	17.678(2)	144.1	5.7620	2.17791
A0.3	3.068	17.677(2)	144.09	5.7617	1.68330
A0.4	3.066	17.679(3)	143.92	5.7661	2.00547

Numbers in parentheses are estimated standard deviations in the Rietveld refinements.

high-purity samples, polished and etched surfaces of the A0.2, A0.3 and A0.4 samples were investigated by FE-SEM microscopy. As seen in Fig. 2, duplex microstructure of plate shaped grains and equiaxed grains were distinguished. With increasing the Al content, the length of plate shaped grains was incremented and the grain growth was occurred. The viscosity amounts of Al are presented as a function of temperature in Table 3. As seen, with increasing the temperature, the viscosity of liquid Al is decreased and reached from 1.298 mPa s at the melting point to 0.865 mPa s at the temperature of 927 °C [37]. It was expressed that increase in the Ti content provides an increase in the viscosity of liquid Al whereas with increasing the Si content, viscosity of liquid Al decreases [38]. Therefore, addition of Al could accelerate the diffusion of Ti and Si atoms and then promoted the synthesis of Ti₃SiC₂ at lower temperature. Liquid phase sintering may help distribute the current and heat more uniformly. As the liquid forms, the particle rearrangement and rotating can take place by the reduction of friction between the particles and the capillary forces of liquid as well. Consequently, there is a better densification relative to the solid state sintering [39,40]. In addition, more Al content led to more equiaxed grains. The length of plate shaped grains was reached to approximately 5 μm in the A0.3 and A0.4 samples. Based on the

literature [20,26], the length and width of plate shaped grains of high-purity Ti₃SiC₂ samples could reach to 2–4 times greater than our results which is owing to higher sintering temperature. The effect of Al addition on the synthesis of Ti₃SiC₂ and solid solution of Ti₃(Si_{1-x}Al_x)C₂ was studied from the EDS mapping of Ti, Si and Al (white points) elements on the A0.2 and A0.3 samples which are indicated in Fig. 3. As seen, plate shaped grains had uniform distribution of Si and Ti which indicates formation of Ti₃SiC₂ in the sintered samples. Besides, un-uniform distribution and agglomeration of Al elements were observed throughout both samples which was slightly higher than in the A0.3 samples. As it can be seen, these Al elements were almost agglomerated in the equiaxed grains. According to the EDS results of A and B microzones, which are shown in Fig. 3, large plate shaped grains and equiaxed grains were attributed to the Ti₃SiC₂ and solid solution of Ti₃(Si_{1-x}Al_x)C₂, respectively. This is in a good agreement with the results of Ghosh et al. [41] which reported that the microzones analyzed by EDS experiments, including the intense Al peak and Ti and Si peaks, seems to be solid solution of Ti₃SiC₂ and Al.

Fig. 4 illustrates the backscatter electron FE-SEM micrograph of sample sintered with starting powder mixture of Ti:Si:TiC:Al = 1:1.2:2:0.1 at 1150 °C (A0.1 sample). According to the EDS results corresponding to C-G microzones, presented in the Table 4, it can be said that in addition to the Ti₃SiC₂, Ti₅Si₃ and TiC phases, which identified in the XRD patterns, some ternary and tetrameric compounds were observed. Thermodynamically, ternary compound can be referred to the TiC, SiC and C phases. Also, this ternary compound was located in the Ti₅Si₃C_x phase. Therefore, it can be suggested that Ti₅Si₃C_x could be formed with the reactions between TiC and SiC phases. As it can be observed in Fig. 4, Ti₃SiC₂ phase was formed in the common boundary of Ti₅Si₃C_x and TiC phases and then this is a logical conclusion which formation of Ti₃SiC₂ was the result of Ti₅Si₃C_x and TiC phases.

Nano-laminate nature of Ti₃SiC₂ present in the high-purity samples is shown in Fig. 5. It is clearly seen that these nano-layers were lied on the each other. The damage tolerant property of Ti₃SiC₂ is attributed to these nano-layered structures which can alternately deflect the crack fracture force in the inter-layer and consequently promote the fracture toughness. The arrows, specified in Fig. 5, are the representative of different plastic deformation mechanisms. The formation of kink bands and bending of nano-laminates are clearly observed which is indicative of high

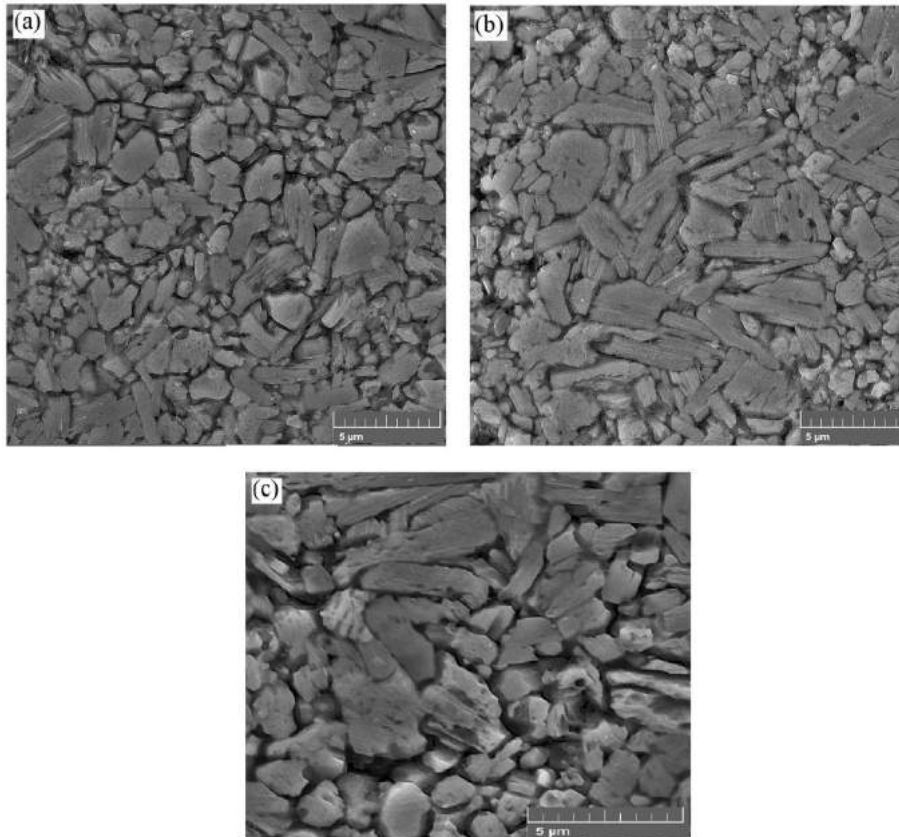


Fig. 2. Secondary electron FE-SEM micrographs of (a) A0.2, (b) A0.3 and (c) A0.4 samples.

Table 3

Viscosity amounts of Al as a function of temperature [37].

Temperature (°C)	677	702	727	752	777	802	827	852	877	902	927
Viscosity (mPa.s)	1.298	1.235	1.178	1.126	1.079	1.035	0.996	0.959	0.925	0.894	0.865

plasticity Ti_3SiC_2 at high temperature.

3.3. Sintering behavior and density

To study the sintering behavior of SPS sintered samples at high temperatures, the displacement curves as a function of time and temperature were used. Fig. 6 illustrates the sintering behavior of A0.4 sample at high temperatures. This displacement directly indicates the sintering shrinkage profile during densification of the compacts. As shown, there was two distinct points in the displacement curves which indicated the initiation (S point) and completion (F point) of densification process. The temperature of initiation and completion of densification process is listed in Table 5. It is apparent that the compact with maximum Al content, began to densify at lower temperature than those with 0.2 and 0.3 mol. The sintering shrinkage of A0.4 compact initiated at the temperature of 985 °C but with decreasing Al content to 0.3 and 0.2 mol, this temperature increased to 1017 °C and 1066 °C, respectively. The sintering shrinkage of A0.4 sample finished at the temperature of 1088 °C, while the shrinkage of A0.3 and A0.2 samples completed at the temperatures of 1112 and 1130 °C, respectively. It can be seen that the Al addition to the starting powder mixture decreased both initiation and completion temperatures of densification and resulted in ≈ 40 °C temperature

difference between the initiation and completion temperatures of samples in compared to each other. These results clearly indicate the enhancing effect of Al content on the densification behavior of samples. Addition of Al was led to the formation of melting bath at ≈ 600 °C and subsequently, acceleration of Ti and Si diffusion in the compacts.

Fig. 7 shows the variation of density and relative density of samples sintered at 1150 °C for 8 min as a function of Al content. The relative densities of samples increased rapidly from 91.28% to 98%–98.5% with appropriate addition of Al. The relative densities of A0.2, A0.3 and A0.4 were 98.02%, 98.3% and 98.48%, respectively. With increasing Al content from 0.2 mol to 0.4, the relative densities enhanced slightly, which confirmed the displacement results at high temperatures. Moreover, the particle refinement induced by ball-milling process can lead to arrangement of atoms on the free surface and then fine particles have lower melting temperatures relative to larger ones [42]. Thermodynamically, sintering is an irreversible process which its driving force is decrease in free energy (through decrease in surface area) and then mass transport to the necking zone promotes with reduction of particle size. Decrease in the particle size provides an increment in the grain boundary and surface area and consequently free surface energy [43]. Therefore, with increasing the free surface energy due to increment of surface energy, sintering could take place at lower sintering temperature.

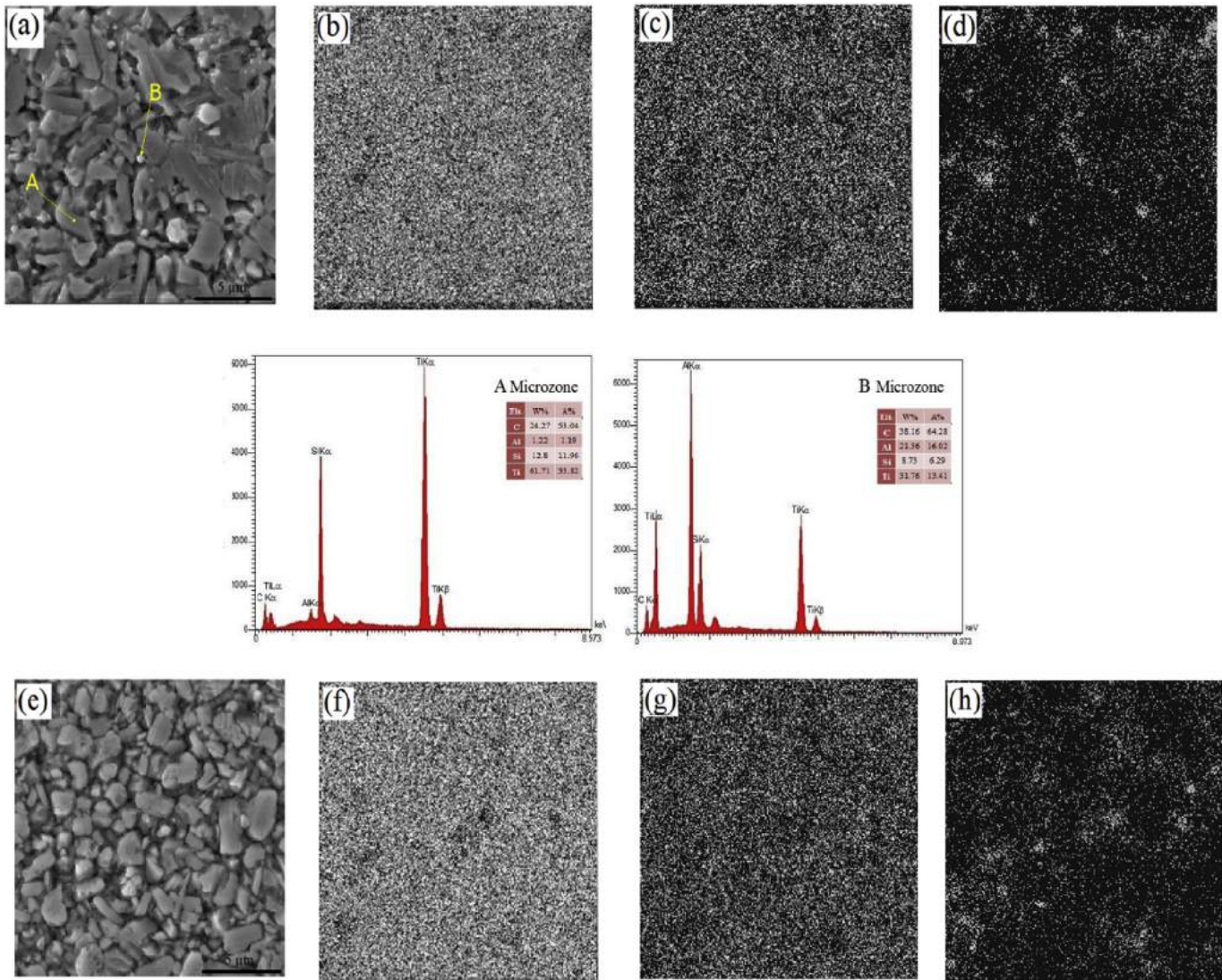


Fig. 3. Secondary electron FE-SEM micrographs and EDS mapping of Ti, Si and Al on the (a–d) A0.2 and (e–h) A0.3 samples, respectively.

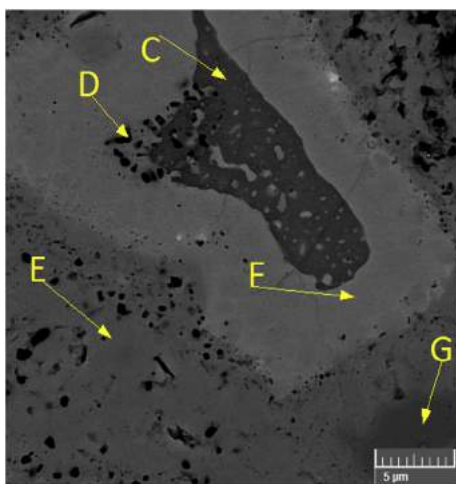


Fig. 4. Backscatter electron FE-SEM micrograph of A0.1 sample.

Table 4

EDS results from C–G microzones.

Microzone	Composition (atomic percent)				Possible phase
	Ti	Si	Al	C	
C	12.78	20.81	2.48	63.92	Ti–Si–C compound
D	17.87	15.83	26.68	39.62	Ti–Si–Al–C compound
E	38.17	12.1	0.43	49.3	Ti ₃ SiC ₂
F	28.1	18.11	1.93	51.86	Ti ₅ Si ₃ C _x
G	43.16	0.22	0.18	56.44	TiC

3.4. Mechanical properties

Fig. 8 (a)–(c) represent the Vickers microhardness of samples as a function of the applied indentation load. It can be observed that at lower loads, especially 0.5 N, the hardness values were high which represents the hardness of mono-crystal as indentation was within one grain. The Vickers microhardness of A0.2 sample was higher than two other samples at low indentation loads. This result

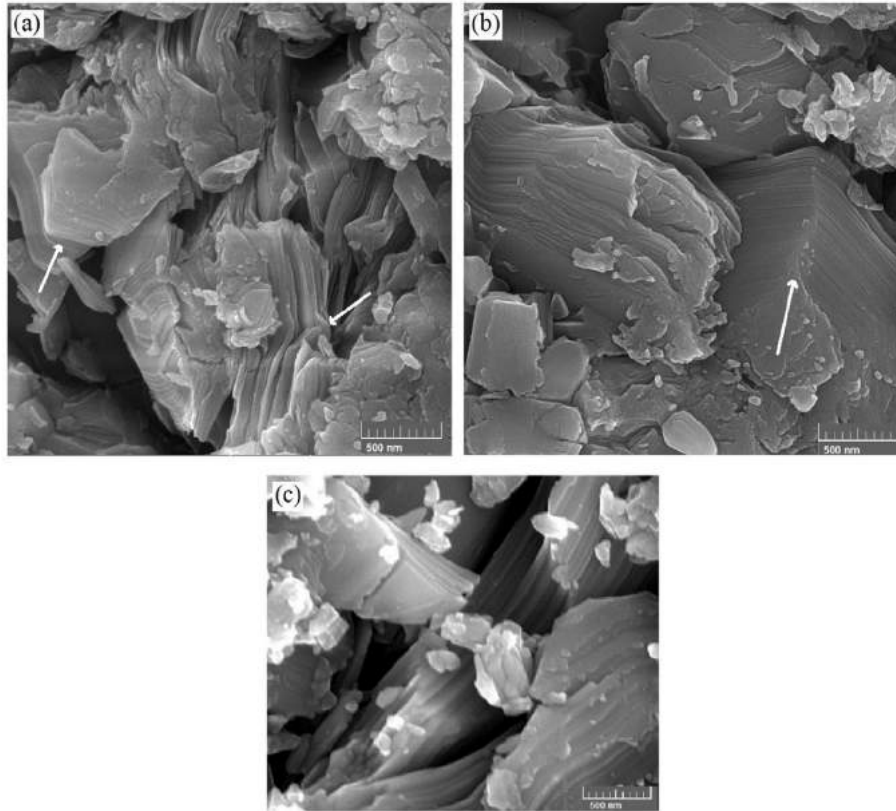


Fig. 5. FE-SEM micrographs of nano-laminated Ti_3SiC_2 in the (a) A0.2, (b) A0.3 and (c) A0.4 samples.

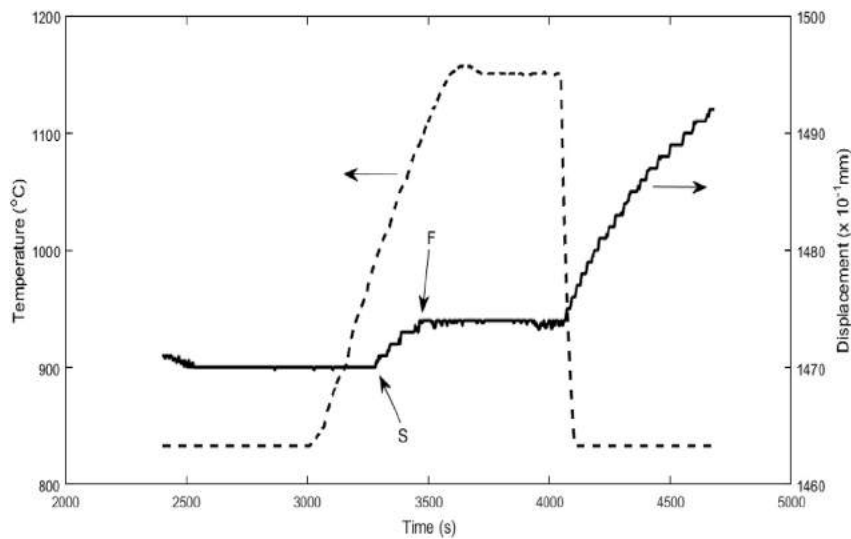


Fig. 6. Sintering behavior of A0.4 sample at high temperatures.

Table 5

Summary of densification process during spark plasma sintering of A0.2, A0.3 and A0.4 samples.

Sample	Initiation Temperature(°C)	Completion Temperature(°C)	Transformation Time from S to F(s)
A0.2	1066	1130	145
A0.3	1017	1112	190
A0.4	985	1088	184

confirmed the finer microstructure of A0.2 sample which shown in the microstructure analysis section. Based on the Hall-Petch equation [44], as the grain size increases, the hardness decreases. Moreover, this decrease can be attributed to the Al content. Zhou et al. [45] reported that with addition of 0.25 mol Si to the ternary compound Ti_3AlC_2 , the Vickers hardness was promoted but this was lower than that of Ti_3SiC_2 . As discussed before, with increasing the Al content in the starting powder mixture, more equiaxed grains

were observed and it can be concluded that addition of 0.3 and 0.4 mol Al in the starting powder mixtures led to decreasing the microhardness relative to A0.2 sample at low loads. As indentation load increased, the hardness decreased for all samples and the microhardness values became independent of indentation load and grain size. The Vickers microhardness of A0.2, A0.3 and A0.4 samples at 10 N load were 6.94 ± 0.51 GPa, 6.78 ± 0.76 GPa and 6.85 ± 0.62 GPa, respectively. The obtained results are similar to each other and in a relatively good agreement with the value reported by Goto and Hirai (6 GPa) at 10 N [46]. In addition, Ghosh et al. [33] obtained a hardness value of 5.96 ± 0.19 GPa for the nearly single phase Ti_3SiC_2 at 10 N. The promoted Vickers microhardness obtained in the high-purity samples could be related to the solid solution hardening. Gao et al. [35] reported that the Vickers microhardness of Ti_3SiC_2 increased from 4.3 GPa at 10 N load to 5.2 GPa for solid solution of $\text{Ti}_3(\text{Al}_{1-x}\text{Si}_x)\text{C}_2$ with $x = 0.4$ at

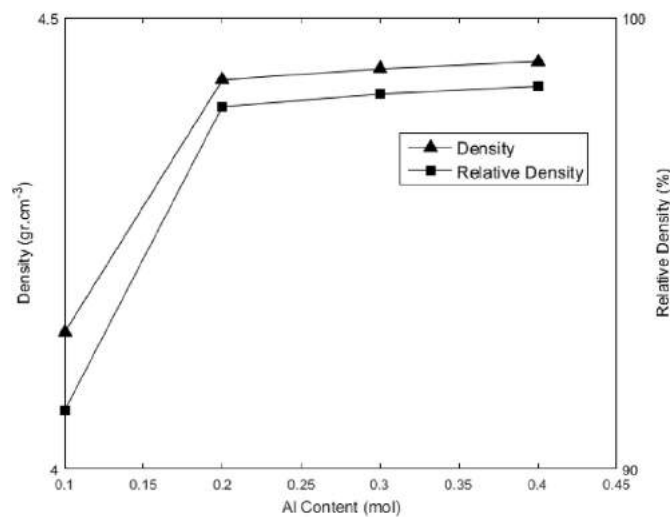


Fig. 7. Effect of Al content on the density of A0.1, A0.2, A0.3 and A0.4 samples, sintered at 1150 °C for 8 min.

the starting powder mixture. The Vickers microhardness of A0.1 sample obtained 8.18 ± 1.19 GPa at load of 2 N. The high standard deviation value observed in the A0.1 sample can be related to the hardness values of distinct components with high values related to the TiC (28–35 [47]) and low ones related to the pure Ti_3SiC_2 . Abderrazak et al. [48] reported a hardness value of 9.37 GPa at 5 N load for a final product contained 57.9 wt% Ti_3SiC_2 , 35.76 wt% TiC and 5.02 wt% TiSi_2 .

Fig. 9 represents the optical micrographs of Vickers indentation conducted at 0.5, 5, 10 N on polished surface of A0.2 sample. It is clearly seen that at low indentation, no plastic deformation was carried out around the indentation mark, but with increasing the indentation load, the pile up of the material and damage were observed in the neighborhood of the indentation that normally occurs in the metals. When the indentation load was increased from 5 N to 10 N, the material piled up around the indentation mark, got more apparent. Also, no cracks were observed in the neighborhood of the indentation mark and the damage was confined to the immediate vicinity of the indentations.

Table 6 presents the longitudinal sound velocity (V_l) and the Young's modulus results of SPS sintered samples. It is apparent that the longitudinal sound velocity and Young's modulus increased with enhancing densification in the A0.2, A0.3 and A0.4 samples. The maximum amounts of longitudinal sound velocity and Young's modulus were attributed to the A0.4 sample which had maximum Al content among the samples and subsequently, the best densification behavior. These results confirmed the Rietveld refinement results. Gao et al. [35] expressed that with increasing Si content in the $\text{Ti}_3(\text{Al}_{1-x}\text{Si}_x)\text{C}_2$ solid solution, the Young's modulus was increased due to stronger M-A bonding. Since there were no significant variation between c-lattice parameters for high-purity Ti_3SiC_2 samples, then the related Young's modulus amounts were comparable to each other. The Young's modulus of high-purity Ti_3SiC_2 samples are in relatively good agreement with values that were obtained from pulse-echo method ($E = 353$ GPa, $V_l = 9350 \text{ m s}^{-1}$) [49] and RUS results ($E = 343$ GPa, $V_l = 9185 \text{ m s}^{-1}$) [50]. With decreasing the Al content to 0.1 mol (A0.1 sample) and subsequently increasing the secondary phases, the longitudinal

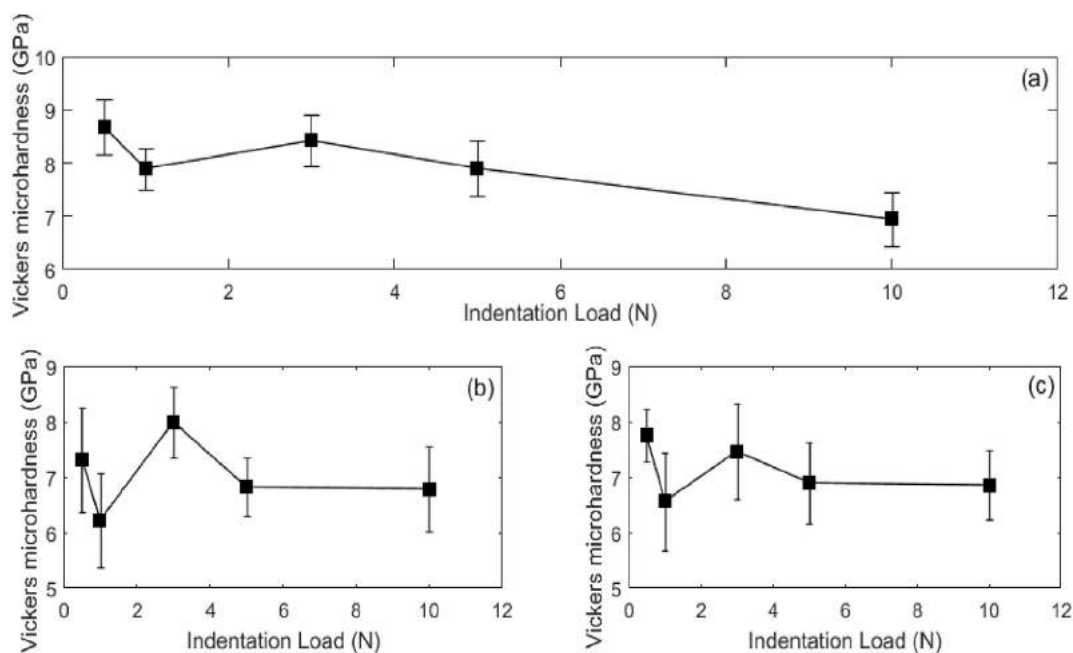


Fig. 8. The Vickers microhardness as a function of the applied indentation load for (a) A0.2, (b) A0.3 and (c) A0.4 samples.

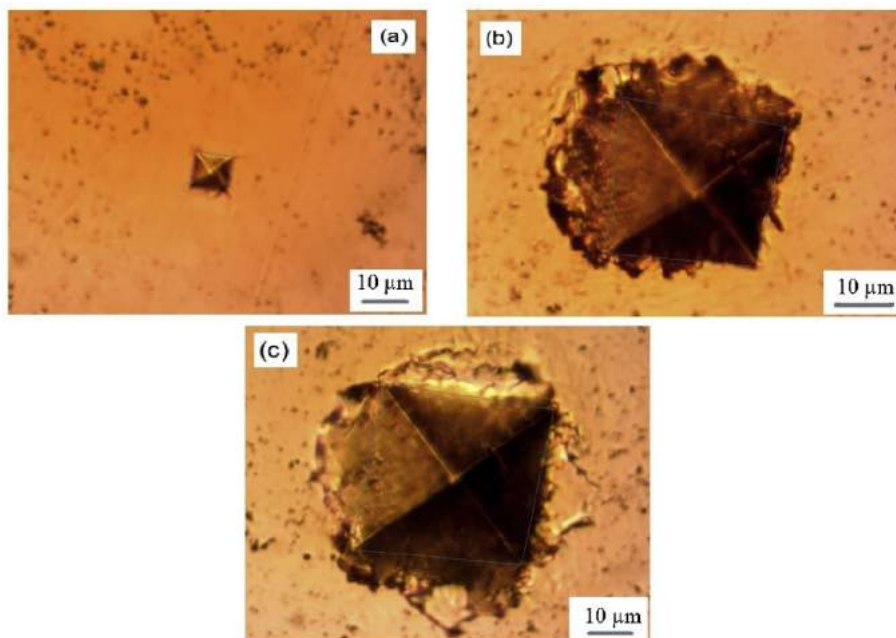


Fig. 9. Optical micrographs of Vickers indentation conducted on A0.2 sample at the loads of (a) 0.5, (b) 5 and (c) 10 N.

Table 6

The results of the longitudinal sound velocity and the Young's modulus of A0.1, A0.2, A0.3 and A0.4 samples.

Sample	A0.1	A0.2	A0.3	A0.4
Longitudinal sound velocity (m.s ⁻¹)	7985.5	9314.33	9323.66	9328.87
Young's modulus (GPa)	235.02	346.46	347.81	348.92

sound velocity and Young's modulus was diminished. The specific stiffness (E/ρ) of high-purity Ti_3SiC_2 samples ($\approx 78 \text{ GPa cm}^3 \text{ g}^{-1}$) was very close to Si_3N_4 one which is higher than many metal and ceramic compounds [5].

4. Conclusion

High-purity single-phase Ti_3SiC_2 samples were synthesized by spark plasma sintering of $\text{Ti}:\text{Si}:\text{TiC}:\text{Al} = 1:1:1.2:x$ (0.2–0.4) at the sintering temperature of 1150 °C under unidirectional pressure of 40 MPa for 8 min. Appropriate addition of Al enhanced the densification process and decreased both initiation and completion temperatures of densification. Moreover, the addition of Al decreased the optimum sintering temperature. With decreasing the Al content, Ti_3SiC_2 was formed besides TiC and Ti_5Si_3 phases as auxiliary phases. The Rietveld refinement and standard additive method used to determine the weight percentage of Ti_3SiC_2 , TiC and Ti_5Si_3 phases, led to obtaining different results which was caused by many and strongly overlapping peaks. The Vickers microhardness values of high-purity Ti_3SiC_2 samples were determined $\approx 6.8 \text{ GPa}$ at 10 N load. The highest Young's modulus was about 349 GPa and decreased with lowering Al content and density.

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